

L Number	Hits	Search Text	DB	Time stamp
1	36	"4709225"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:22
2	46139	ion\$1 adj beam\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:22
3	24	"4709225" and "36"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:22
4	0	"4709225" and (ion\$1 adj beam\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:23
5	3	"6426903"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:23
6	2	(ion\$1 adj beam\$1) and "6426903"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:24
7	155091	438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:25
8	1613552	capacit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:25
9	1665	(ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:25
10	1056	((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:26
11	766	((((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric) and chang\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:27
12	66	on adj chip\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:27

13	0	(((((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric) and chang\$4) and (on adj chip\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:27
14	590	(((((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric) and chang\$4) and integrated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:28
15	352	(((((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric) and chang\$4) and integrated) and constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:29
16	346	(((((ion\$1 adj beam\$1) and 438/\$.ccls. and capacit\$5) and dielectric) and chang\$4) and integrated) and constant) and method	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:31
17	343	ion adj beam adj exposure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:32
18	85968	dielectric adj constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:41
19	3	dielectric adj constant adj modification	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:33
21	0	(ion adj beam adj exposure) and ((dielectric adj constant) near modification\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:34
20	16	(dielectric adj constant) near modification\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:36
22	7	(ion adj beam adj exposure) and (dielectric adj constant)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:39
23	2154649	capacitance adj change	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:40
24	3178	capacitance adj change	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:40

25	0	(capacitance adj change) and (ion adj beam adj exposure)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:40
26	297	dielectric adj constant adj change	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:41
27	0	(ion adj beam adj exposure) and (dielectric adj constant adj change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:47
28	1		USPAT	2004/08/24 14:44
29	1		USPAT	2004/08/24 14:44
30	1		USPAT	2004/08/24 14:45
31	1		USPAT	2004/08/24 14:46
32	85968	dielectric adj constant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:48
33	45991	ion adj beam\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:49
34	1989937	change	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:49
35	1942	(dielectric adj constant) near change	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:50
36	31	(ion adj beam\$1) and ((dielectric adj constant) near change)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:54
37	360	capacitance adj adjustment\$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:55
38	0	(dielectric adj constant adj change) and (capacitance adj adjustment\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/24 14:55